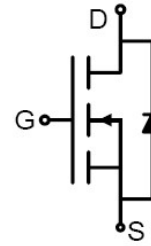


Feature

- 20V,2.8A
 $R_{DS(ON)} < 55m\Omega @ V_{GS}=4.5V$
 $R_{DS(ON)} < 80m\Omega @ V_{GS}=2.5V$
- Advanced Trench Technology
- Lead free product is acquired



Schematic Diagram

Application

- Interfacing Switching
- Load Switching
- Power management



SOT-323 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
55N20	AP55N20N3	Sot-323	7 inch	-	3000

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 10	V
Continuous Drain Current ($T_a = 25^\circ\text{C}$)	I_D	2.8	A
Continuous Drain Current ($T_a = 70^\circ\text{C}$)	I_D	2	A
Pulsed Drain Current	I_{DM}	12	A
Power Dissipation	P_D	0.25	W
Thermal Resistance from Junction to Ambient ⁽⁴⁾	$R_{\theta JA}$	500	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	20	-	-	V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 20V, V_{GS} = 0V$	-	-	1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0V$	-	-	± 100	nA
Gate threshold voltage ⁽³⁾	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.3	0.7	1.0	V
Drain-source on-resistance ⁽³⁾	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 2.8A$	-	48	55	m Ω
		$V_{GS} = 2.5V, I_D = 2A$	-	64	80	
Dynamic characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$	-	184	-	pF
Output Capacitance	C_{oss}		-	38	-	
Reverse Transfer Capacitance	C_{rss}		-	28	-	
Switching characteristics						
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 10V, I_D = 2.8A,$ $V_{GS} = 4.5V, R_G = 10\Omega$	-	2.3	-	ns
Turn-on rise time	t_r		-	3.1	-	
Turn-off delay time	$t_{d(off)}$		-	9.2	-	
Turn-off fall time	t_f		-	2.5	-	
Total Gate Charge	Q_g	$V_{DS} = 10V, I_D = 2.8A,$ $V_{GS} = 4.5V$	-	2.7	-	nC
Gate-Source Charge	Q_{gs}		-	0.4	-	
Gate-Drain Charge	Q_{gd}		-	0.5	-	
Source-Drain Diode characteristics						
Diode Forward voltage ⁽³⁾	V_{DS}	$V_{GS} = 0V, I_S = 2.8A$	-	-	1.2	V
Diode Forward current ⁽⁴⁾	I_S		-	-	2.8	A

Notes:

1. Repetitive Rating: pulse width limited by maximum junction temperature
2. Pulse Test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. Surface Mounted on FR4 Board, $t_s \leq 10$ sec

Test Circuit

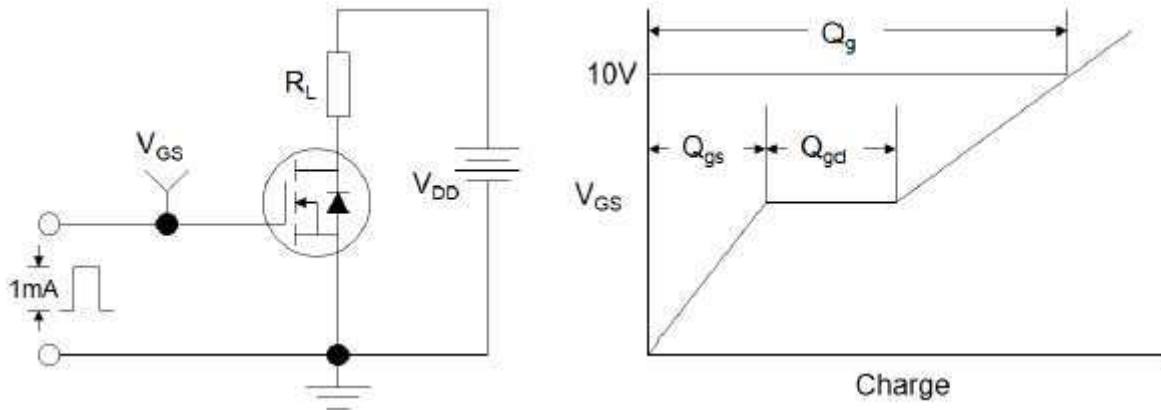


Figure1:Gate Charge Test Circuit & Waveform

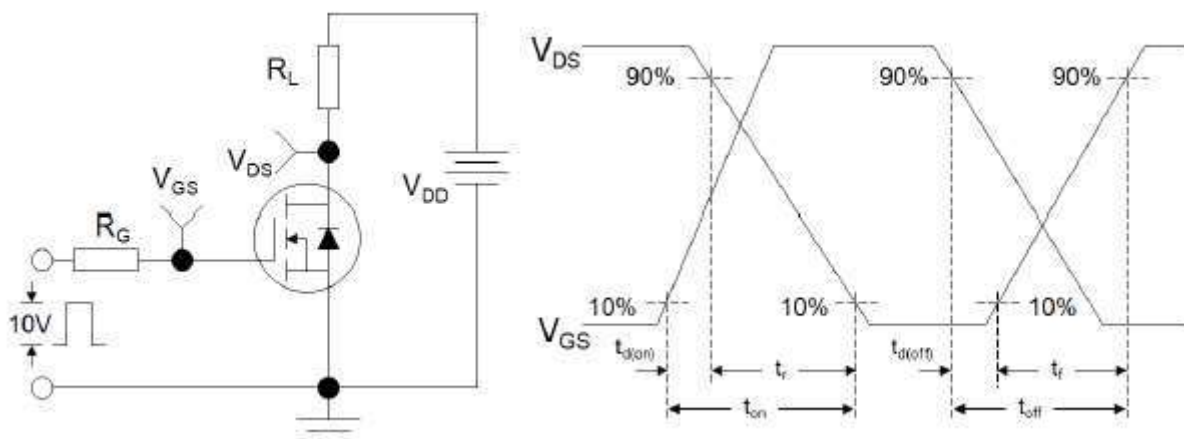


Figure 2: Resistive Switching Test Circuit & Waveforms

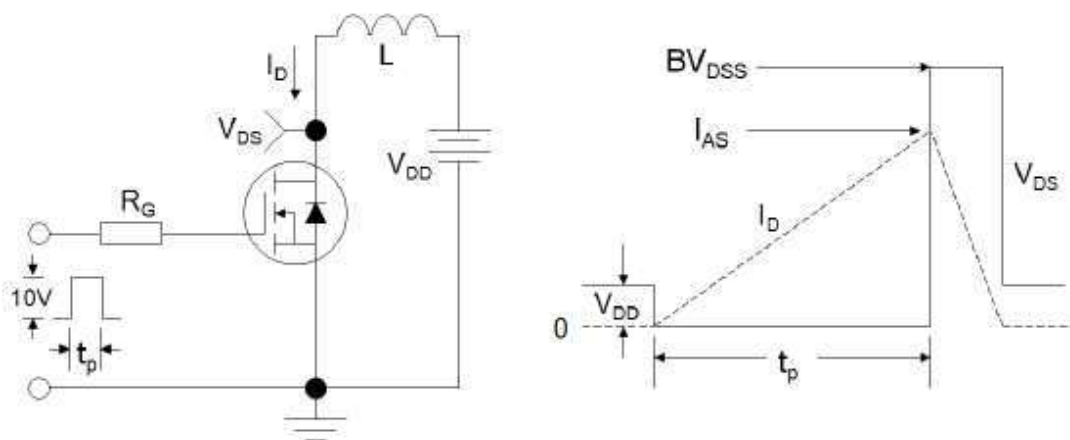


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

Typical Performance Characteristics

Figure 1: Output Characteristics

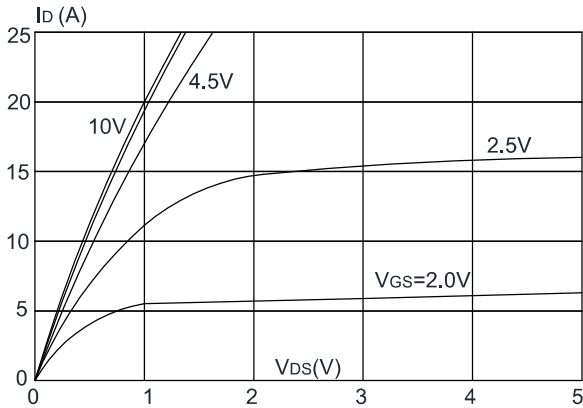


Figure 2: Typical Transfer Characteristics

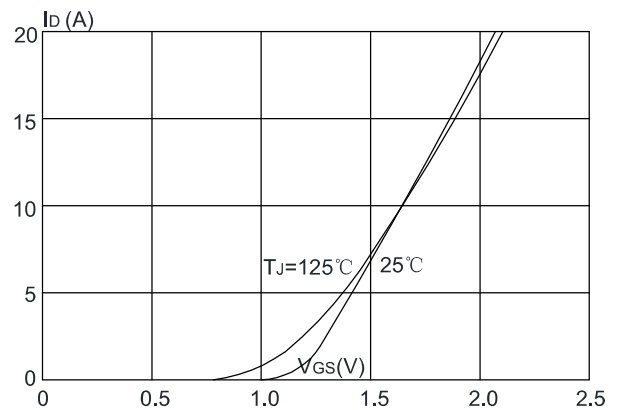


Figure 3: On-resistance vs. Drain Current

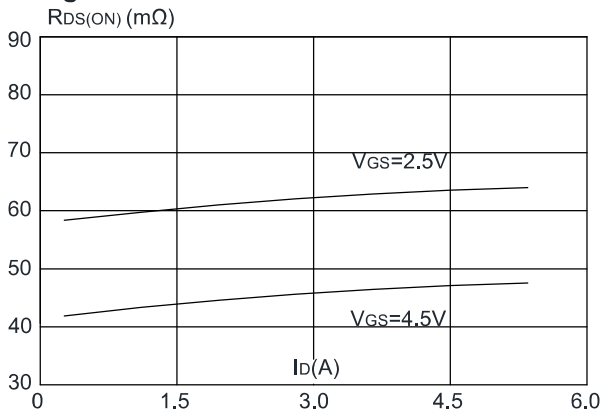


Figure 4: Body Diode Characteristics

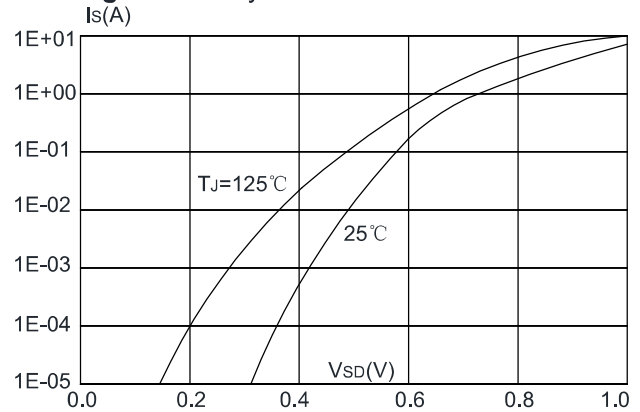


Figure 5: Gate Charge Characteristics

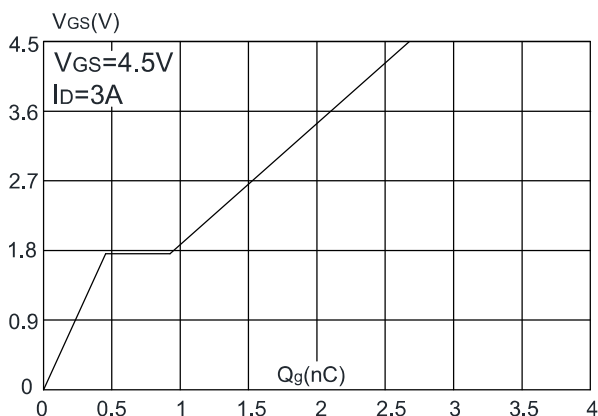


Figure 6: Capacitance Characteristics

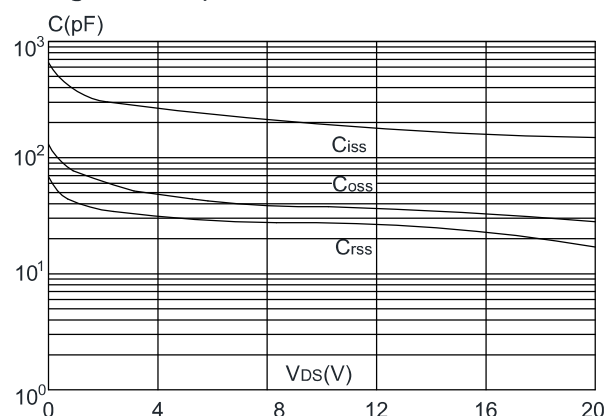


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

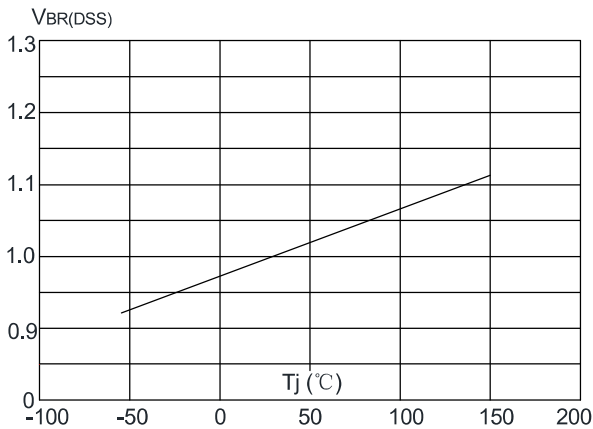


Figure 8: Normalized on Resistance vs. Junction Temperature

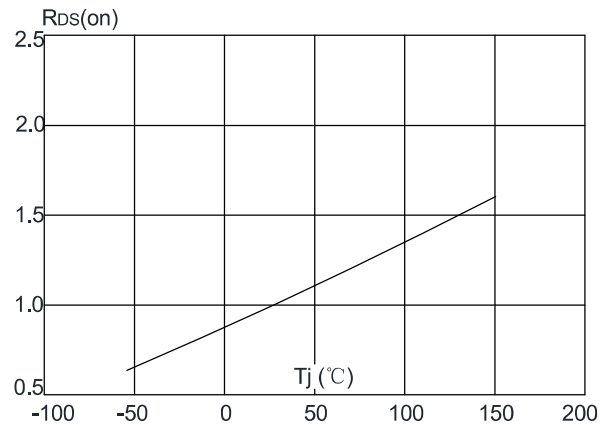


Figure 9: Maximum Safe Operating Area

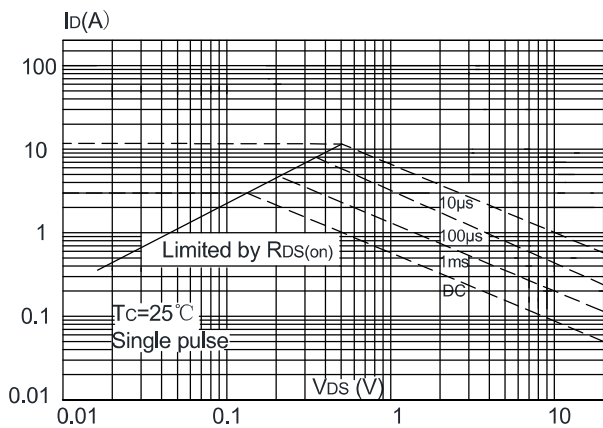


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

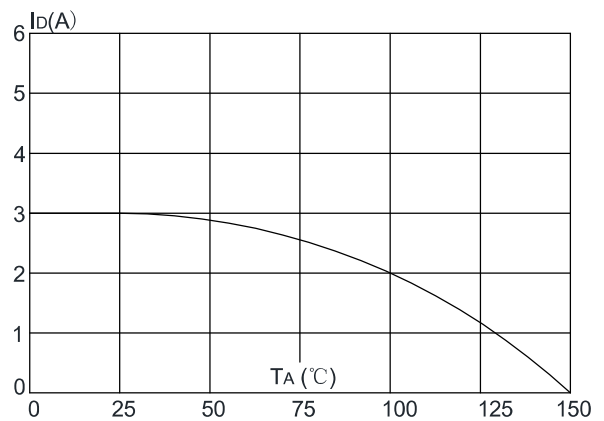
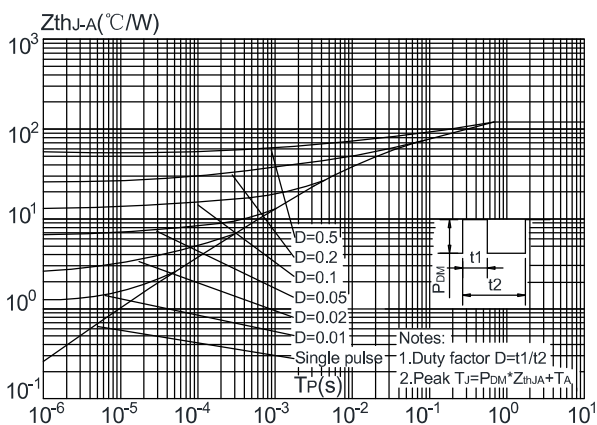
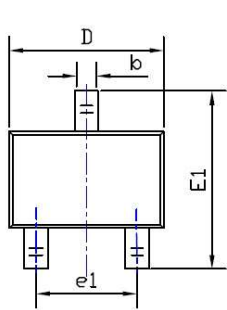


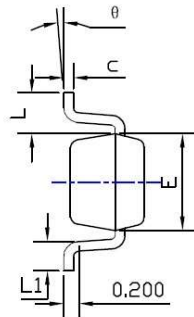
Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



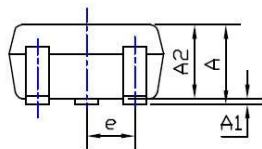
SOT-323 Package Information



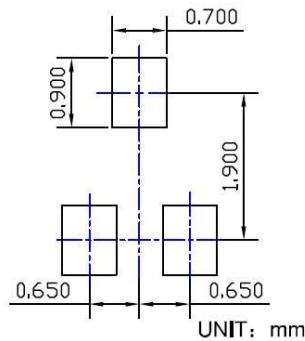
TOP VIEW



SIDE VIEW



SIDE VIEW



UNIT: mm

SUGGESTED SOLDER PAD LAYOUT

SYMBOL	DIMENSIONS					
	INCHES			Millimeter		
	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.
A	0.035	----	0.043	0.900	----	1.100
A1	0.000	----	0.004	0.000	----	0.100
A2	0.035	0.037	0.039	0.900	0.950	1.000
b	0.006	0.012	0.016	0.150	0.300	0.400
c	0.004	----	0.010	0.100	----	0.250
D	0.071	0.079	0.087	1.800	2.000	2.200
E	0.045	0.049	0.053	1.150	1.250	1.350
E1	0.085	0.091	0.096	2.150	2.300	2.450
e	0.026TYP			0.650TYP		
e1	0.047	0.051	0.055	1.200	1.300	1.400
L	0.021REF			0.525REF		
L1	0.010	0.014	0.018	0.260	0.360	0.460
theta	0°	----	8°	0°	----	8°

NOTE:

- 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
- 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.